



SURFACE MOUNT TRANSISTORS

T-27-09

NPN TRANSISTORS - SOT-23 PACKAGE

310 mW DISSIPATION RATING (See Note 4)

CHARACTERISTICS @ T_A 25°C

OPERATING/STORAGE TEMPERATURE -55°C to +150°C

Type Number	Marking Code	V _{CEO}	h _{FE} @	V _{CE} /I _C	V _{CE SAT} @	I _C /I _B	I _{CES} @	V _{CE}	f _T @	V _{CE} /I _C	C _{OB} @	V _{CB}
		Volts	V/mA	max.V	mA/mA	max.nA	V	MHz	V/mA	max.pF	V	
IMBT3903	1M	40	50-150	1/10	0.3	50/5	50 ⁽²⁾	30	min.250	20/10	4	5
IMBT3904	1N	40	100-300	1/10	0.3	50/5	50 ⁽²⁾	30	min.300	20/10	4	5
IMBT4400	6T	40	50-150	1/150	0.75	500/50	100 ⁽³⁾	35	min.200	10/20	6.5	5
IMBT4401	6U	40	100-300	1/150	0.75	500/50	100 ⁽³⁾	35	min.250	10/20	6.5	5
IMBT2222	6R	30	100-300	10/150	1.6	500/50	10 ⁽¹⁾	50	min.250	20/20	8	10
IMBT2222A	6S	40	100-300	10/150	1.0	500/50	10 ⁽¹⁾	60	min.300	20/20	8	10

(1) I_{CBO} (2) I_{CEV} @ V_{EB} = 3V (3) I_{CEV} @ V_{EB} = 0.4V
 (4) MOUNTED ON .7mm THICK CERAMIC SUBSTRATE OF MIN AREA OF 2.5 cm² - T_{SB} = 50°C

NPN TRANSISTORS - EUROPEAN TYPES - TO-236 PACKAGE

CHARACTERISTICS @ T_A 25°C

Type Number	Marking Code	V _{CEO}	h _{FE} @	V _{CE} /I _C	V _{CE SAT} @	I _C /I _B	I _{CES} @	V _{CE}	f _T @	V _{CE} /I _C	C _{OB} @	V _{CB}
		Volts	V/mA	max.V	mA/mA	max.nA	V	MHz	V/mA	max.pF	V	
BC817-16	6A	45	100-250	1/100	0.7	500/50	100	45	100	5/10	12	10
BC817-25	6B	45	160-400	1/100	0.7	500/50	100	45	100	5/10	12	10
BC817-40	6C	45	250-600	1/100	0.7	500/50	100	45	100	5/10	12	10
BC846A	1A	65	110-220	5/2	0.6	100/5	15	80	300	5/10	6	10
BC846B	1B	65	200-450	5/2	0.6	100/5	15	80	300	5/10	6	10
BC847A	1E	45	110-220	5/2	0.6	100/5	15	50	300	5/10	6	10
BC847B	1F	45	200-450	5/2	0.6	100/5	15	50	300	5/10	6	10
BC847C	1G	45	420-800	5/2	0.6	100/5	15	50	300	5/10	6	10
BC848A	1J	30	110-220	5/2	0.6	100/5	15	30	300	5/10	6	10
BC848B	1K	30	200-450	5/2	0.6	100/5	15	30	300	5/10	6	10
BC848C	1L	30	420-800	5/2	0.6	100/5	15	30	300	5/10	6	10

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		Volts	V/mA	max.V	mA/mA	max.nA	V	MHz	V/mA	max.pF	V	
IMBT2907	5P	40	100-300	10/150	1.6	500/50	20 ⁽¹⁾	50	min.200	20/50	8	10
IMBT2907A	5R	60	100-300	10/150	1.6	500/50	10 ⁽¹⁾	50	min.200	20/50	8	10
IMBT3905	3M	40	50-150	1/10	0.4	50/5	50 ⁽²⁾	30	min.200	20/10	4.5	5
IMBT3906	3N	40	100-300	1/10	0.4	50/5	50 ⁽²⁾	30	min.250	20/10	4.5	5
IMBT4402	5T	40	50-150	1/150	0.75	500/50	100 ⁽³⁾	35	min.150	10/20	8.5	5
IMBT4403	5U	40	100-300	1/150	0.75	500/50	100 ⁽³⁾	35	min.200	10/20	8.5	5
IMBTA55	5M	60	min.50	1/100	0.25	100/10	100 ⁽¹⁾	60	min.100	2/10	—	—
IMBTA56	5N	80	min.50	1/100	0.25	100/10	100 ⁽¹⁾	80	min.100	2/10	—	—

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		Volts	V/mA	max.V	mA/mA	max.nA	V	MHz	V/mA	max.pF	V	
BC807-16	5A	45	100-250	1/100	0.7	500/50	100	45	100	5/10	12	10
BC807-25	5B	45	160-400	1/100	0.7	500/50	100	45	100	5/10	12	10
BC807-40	5C	45	250-600	1/100	0.7	500/50	100	45	100	5/10	12	10
BC856A	3A	65	110-220	5/2	0.65	100/5	15	80	150	5/10	6	10
BC856B	3B	65	200-450	5/2	0.65	100/5	15	80	150	5/10	6	10
BC857A	3E	45	110-220	5/2	0.65	100/5	15	50	150	5/10	6	10
BC857B	3F	45	200-450	5/2	0.65	100/5	15	50	150	5/10	6	10
BC857C	3G	45	420-800	5/2	0.65	100/5	15	50	150	5/10	6	10
BC858A	3J	30	110-220	5/2	0.65	100/5	15	30	150	5/10	6	10
BC858B	3K	30	200-450	5/2	0.65	100/5	15	30	150	5/10	6	10
BC858C	3L	30	420-800	5/2	0.65	100/5	15	30	150	5/10	6	10